

15 V low VCEsat NPN/PNP transistor 17 February 2022

1. General description

NPN/PNP low V_{CEsat} transistor pair in a SOT363 (SC-88) very small Surface-Mounted Device (SMD) plastic package. .

2. Features and benefits

- Low collector-emitter saturation voltage
- High current capability
- Replaces two SC-70 packaged low V_{CEsat} transistors on same PCB area
- Reduces required PCB area
- Reduced pick and place costs.
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- General purpose switching and muting
- Low frequency driver circuits •
- LCD backlighting
- Supply line switching circuits
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

4. Quick reference data

Table 1. Quick	reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	unless otherwise speci	fied; for the PNP transistor with negativ	e polari	ty			
V _{CEO}	collector-emitter voltage	open base		-	-	15	V
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	1	А
TR1 (NPN)		•					
R _{CEsat}	collector-emitter saturation resistance	I_{C} = 500 mA; I_{B} = 50 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C		-	300	500	mΩ
TR2 (PNP)		·					
R _{CEsat}	collector-emitter saturation resistance	I _C = -500 mA; I _B = -50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C		-	300	500	mΩ

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5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1		C1 B2 E2
2	B1	base TR1		
3	C2	collector TR2		
4	E2	emitter TR2		
5	B2	base TR2		 E1 B1 C2
6	C1	collector TR1	TSSOP6 (SOT363)	sym139

6. Ordering information

Table 3. Ordering information						
Type number	Package)				
	Name	Description	Version			
PBSS2515YPN-Q	TSSOP6	plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS2515YPN-Q	N8%

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or unless otherwise specified	; for the PNP transistor with neg	ative polarity	I	-	
V _{CBO}	collector-base voltage	open emitter		-	15	V
V _{CEO}	collector-emitter voltage	open base		-	15	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	500	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	1	А
I _{BM}	peak base current			-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C		-	200	mW
Per device	I					_
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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9. Thermal characteristics

Table 6. Therma	al characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	416	K/W

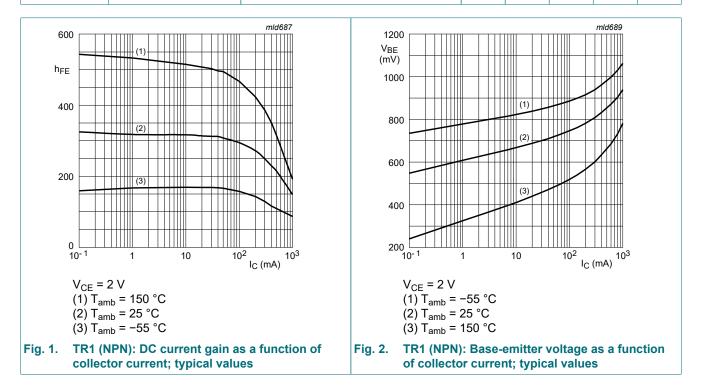
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

10. Characteristics

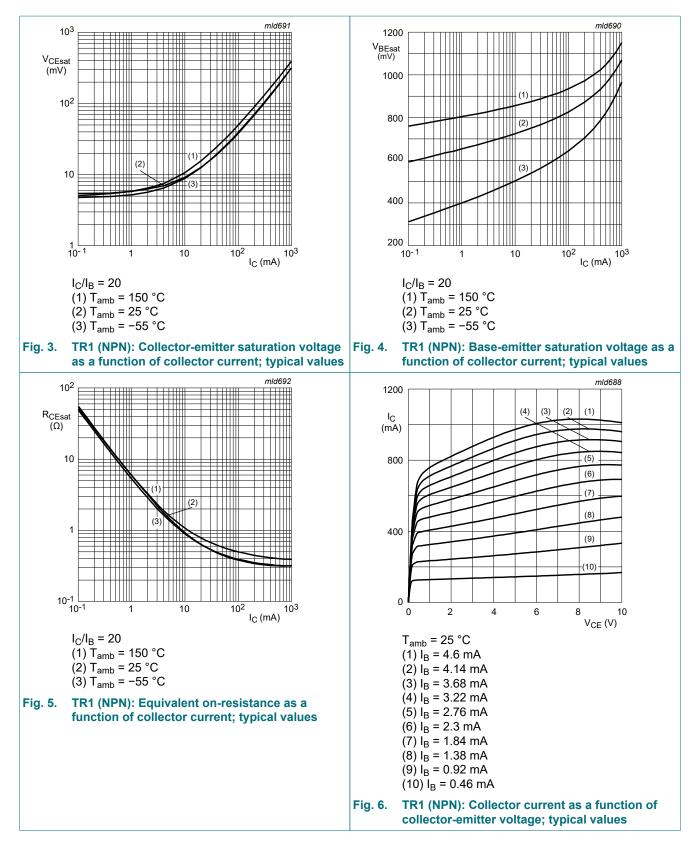
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per transist	tor unless otherwise specif	fied; for the PNP transistor with negative	polarity			
I _{CBO}	collector-base cut-off	V _{CB} = 15 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 15 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
TR1 (NPN)		· · ·	I			
h _{FE}	DC current gain	V_{CE} = 2 V; I _C = 10 mA; T _{amb} = 25 °C	200	-	-	
		V_{CE} = 2 V; I _C = 100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	150	-	-	
		V_{CE} = 2 V; I _C = 500 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	90	-	-	
V _{CEsat}	collector-emitter	I _C = 10 mA; I _B = 0.5 mA; T _{amb} = 25 °C	-	-	25	mV
	saturation voltage	I _C = 200 mA; I _B = 10 mA; T _{amb} = 25 °C	-	-	150	mV
		$I_{C} = 500 \text{ mA}; I_{B} = 50 \text{ mA}; \text{ pulsed}; t_{p} \le 1000 \text{ mA}; t_{p} \ge 1000 \text{ mA}$	-	-	250	mV
R _{CEsat}	collector-emitter saturation resistance	$300 \ \mu s; \delta ≤ 0.02; T_{amb} = 25 \ °C$	-	300	500	mΩ
V _{BEsat}	base-emitter saturation voltage	-	-	-	1.1	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I _C = 100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	0.9	V
f _T	transition frequency	V_{CE} = 5 V; I _C = 100 mA; f = 100 MHz; T _{amb} = 25 °C	250	420	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	4.4	6	pF
TR2 (PNP)		L I		I		
h _{FE}	DC current gain	V_{CE} = -2 V; I _C = -10 mA; T _{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I _C = -100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	150	-	-	
		V_{CE} = -2 V; I _C = -500 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	90	-	-	

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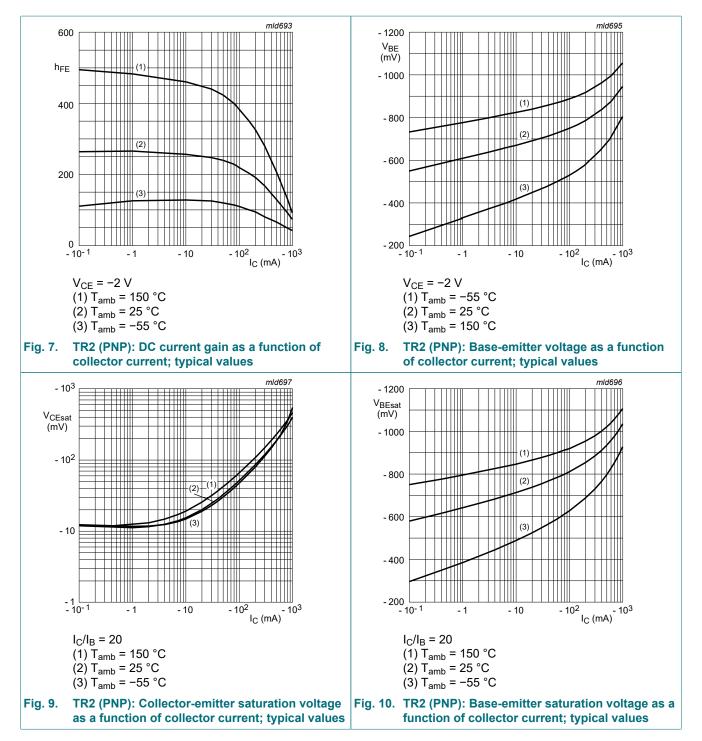
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEsat}	collector-emitter	I_{C} = -10 mA; I_{B} = -0.5 mA; T_{amb} = 25 °C		-	-	-25	mV
	saturation voltage	I_{C} = -200 mA; I_{B} = -10 mA; T_{amb} = 25 °C		-	-	-150	mV
		I_{C} = -500 mA; I_{B} = -50 mA; pulsed; t_{p} ≤		-	-	-250	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C		-	300	500	mΩ
V _{BEsat}	base-emitter saturation voltage			-	-	-1.1	V
V _{BEon}	base-emitter turn-on voltage	V _{CE} = -2 V; I _C = -100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C		-	-	-0.9	V
f _T	transition frequency	V _{CE} = -5 V; I _C = -100 mA; f = 100 MHz; T _{amb} = 25 °C		100	280	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C		-	-	10	pF



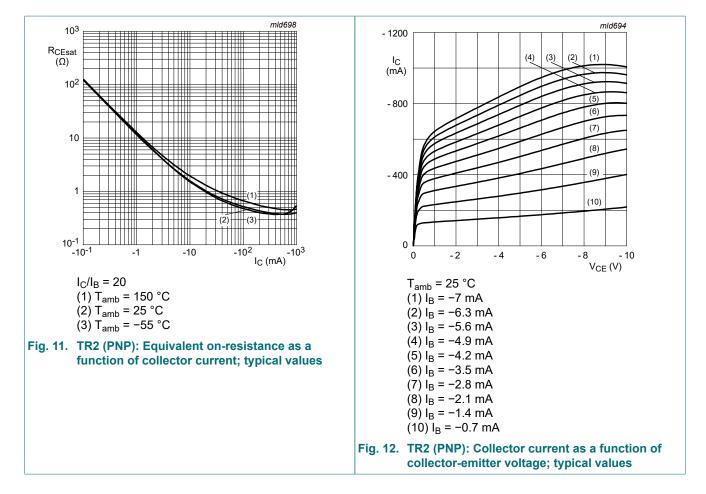
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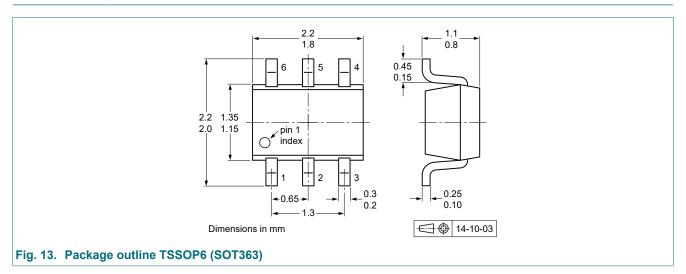


11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

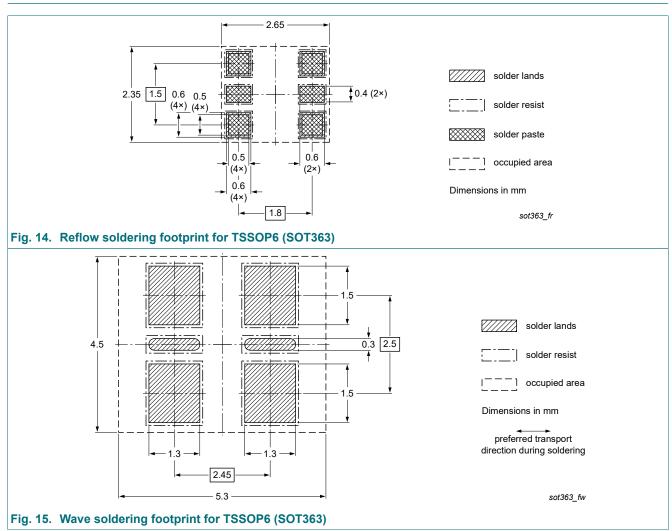
12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS2515YPN-Q v.1	20220217	Product data sheet	-	-		

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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